

製品概要

FCP165N65S3: Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 19 A, 165 mΩ, TO-220

技術情報は、データシートをご参照ください。

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

特長

- 700 V @ $T_J = 150\text{ }^\circ\text{C}$
- Ultra Low Gate Charge (Typ. $Q_g = 39\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss}(\text{eff.}) = 341\text{ pF}$)
- Internal Gate Resistance: 4.6 Ω
- Optimized Capacitance
- Typ. $R_{DS}(\text{on}) = 140\text{ m}\Omega$
- 100% Avalanche Tested
- RoHS Compliant

アプリケーション

- Computing
- Consumer
- Industrial

利点

- Higher system reliability at low temperature operation
- Lower switching loss
- Lower switching loss
- Lower peak V_{ds} and lower V_{gs} oscillation
- Lower peak V_{ds} and lower V_{gs} oscillation

最終製品

- Notebook / Desktop computer
- Game Console
- Telecom / Server
- LCD / LED TV
- LED Lighting / Ballast

電氣的仕様

製品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS}(\text{BR})$ Min (V)	V_{GS} Max (V)	$V_{GS}(\text{th})$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS}(\text{on})$ Max @ $V_{GS} = 2.5\text{ V}$ (m Ω)	$R_{DS}(\text{on})$ Max @ $V_{GS} = 4.5\text{ V}$ (m Ω)	$R_{DS}(\text{on})$ Max @ $V_{GS} = 10\text{ V}$ (m Ω)	Q_g Typ @ $V_{GS} = 4.5\text{ V}$ (nC)	Q_g Typ @ $V_{GS} = 10\text{ V}$ (nC)	C_{iss} Typ (pF)	Package Type
FCP165N65S3	1.1335	Pb-free Halide free	Active	N-Channel	Single	650	30	4.5	19	154	-	-	165	-	39	1500	TO-220-3

詳細は、弊社 www.onsemi.jp の営業または販売代理店にお問い合わせください。

8/13/2020 作成